

MOSFET

OptiMOS™ 3 Power-Transistor, 200 V

Features

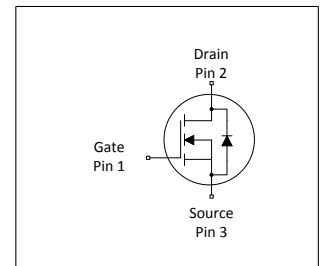
- Ideal for high frequency switching and sync. rec.
- Excellent gate charge x $R_{DS(on)}$ product (FOM)
- Very low on-resistance $R_{DS(on)}$
- N-channel, normal level
- 100% avalanche tested
- Pb-free plating; RoHS compliant
- Halogen-free according to IEC61249-2-21

Product validation

Qualified according to JEDEC Standard

Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS}	200	V
$R_{DS(on),max}$	32	mΩ
I_D	26	A
Q_{oss}	54	nC
$Q_G(0V..10V)$	22	nC



Type / Ordering Code	Package	Marking	Related Links
IPA320N20NM3S	PG-TO 220 FullPAK	320N203S	-

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1 Maximum ratings

at $T_A=25\text{ °C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current	I_D	-	-	26 19	A	$V_{GS}=10\text{ V}$, $T_C=25\text{ °C}$ $V_{GS}=10\text{ V}$, $T_C=100\text{ °C}$
Pulsed drain current ¹⁾	$I_{D,pulse}$	-	-	104	A	$T_C=25\text{ °C}$
Avalanche energy, single pulse ²⁾	E_{AS}	-	-	190	mJ	$I_D=26\text{ A}$, $R_{GS}=25\text{ }\Omega$
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	38	W	$T_C=25\text{ °C}$
Operating and storage temperature	T_j , T_{stg}	-55	-	175	°C	IEC climatic category; DIN IEC 68-1: 55/175/56

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	3.9	°C/W	-

3 Electrical characteristics

at $T_j=25\text{ °C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	200	-	-	V	$V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	2	3	4	V	$V_{DS}=V_{GS}$, $I_D=89\text{ }\mu\text{A}$
Zero gate voltage drain current	I_{DSS}	-	0.1 10	1 100	μA	$V_{DS}=160\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$ $V_{DS}=160\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=125\text{ °C}$
Gate-source leakage current	I_{GSS}	-	1	100	nA	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	27.2	32.0	m Ω	$V_{GS}=10\text{ V}$, $I_D=26\text{ A}$
Gate resistance ³⁾	R_G	-	2.5	-	Ω	-
Transconductance	g_{fs}	-	48	-	S	$ V_{DS} \geq 2 I_D /R_{DS(on)max}$, $I_D=26\text{ A}$

¹⁾ See Diagram 3 for more detailed information

²⁾ See Diagram 13 for more detailed information

³⁾ Defined by design. Not subject to production test.

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance ¹⁾	C_{iss}	-	1800	2300	pF	$V_{GS}=0\text{ V}$, $V_{DS}=100\text{ V}$, $f=1\text{ MHz}$
Output capacitance	C_{oss}	-	140	-	pF	$V_{GS}=0\text{ V}$, $V_{DS}=100\text{ V}$, $f=1\text{ MHz}$
Reverse transfer capacitance	C_{rss}	-	5	-	pF	$V_{GS}=0\text{ V}$, $V_{DS}=100\text{ V}$, $f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	11	-	ns	$V_{DD}=100\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=13\text{ A}$, $R_{G,ext}=1.6\ \Omega$
Rise time	t_r	-	9	-	ns	$V_{DD}=100\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=13\text{ A}$, $R_{G,ext}=1.6\ \Omega$
Turn-off delay time	$t_{d(off)}$	-	21	-	ns	$V_{DD}=100\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=13\text{ A}$, $R_{G,ext}=1.6\ \Omega$
Fall time	t_f	-	4	-	ns	$V_{DD}=100\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=13\text{ A}$, $R_{G,ext}=1.6\ \Omega$

Table 6 Gate charge characteristics²⁾

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	8	-	nC	$V_{DD}=100\text{ V}$, $I_D=13\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge at threshold	$Q_{g(th)}$	-	5	-	nC	$V_{DD}=100\text{ V}$, $I_D=13\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate to drain charge	Q_{gd}	-	3	-	nC	$V_{DD}=100\text{ V}$, $I_D=13\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Switching charge	Q_{sw}	-	5	-	nC	$V_{DD}=100\text{ V}$, $I_D=13\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total ¹⁾	Q_g	-	22	30	nC	$V_{DD}=100\text{ V}$, $I_D=13\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	4.3	-	V	$V_{DD}=100\text{ V}$, $I_D=13\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total, sync. FET	$Q_{g(sync)}$	-	20	-	nC	$V_{DS}=0.1\text{ V}$, $V_{GS}=0\text{ to }10\text{ V}$
Output charge	Q_{oss}	-	54	-	nC	$V_{DD}=100\text{ V}$, $V_{GS}=0\text{ V}$

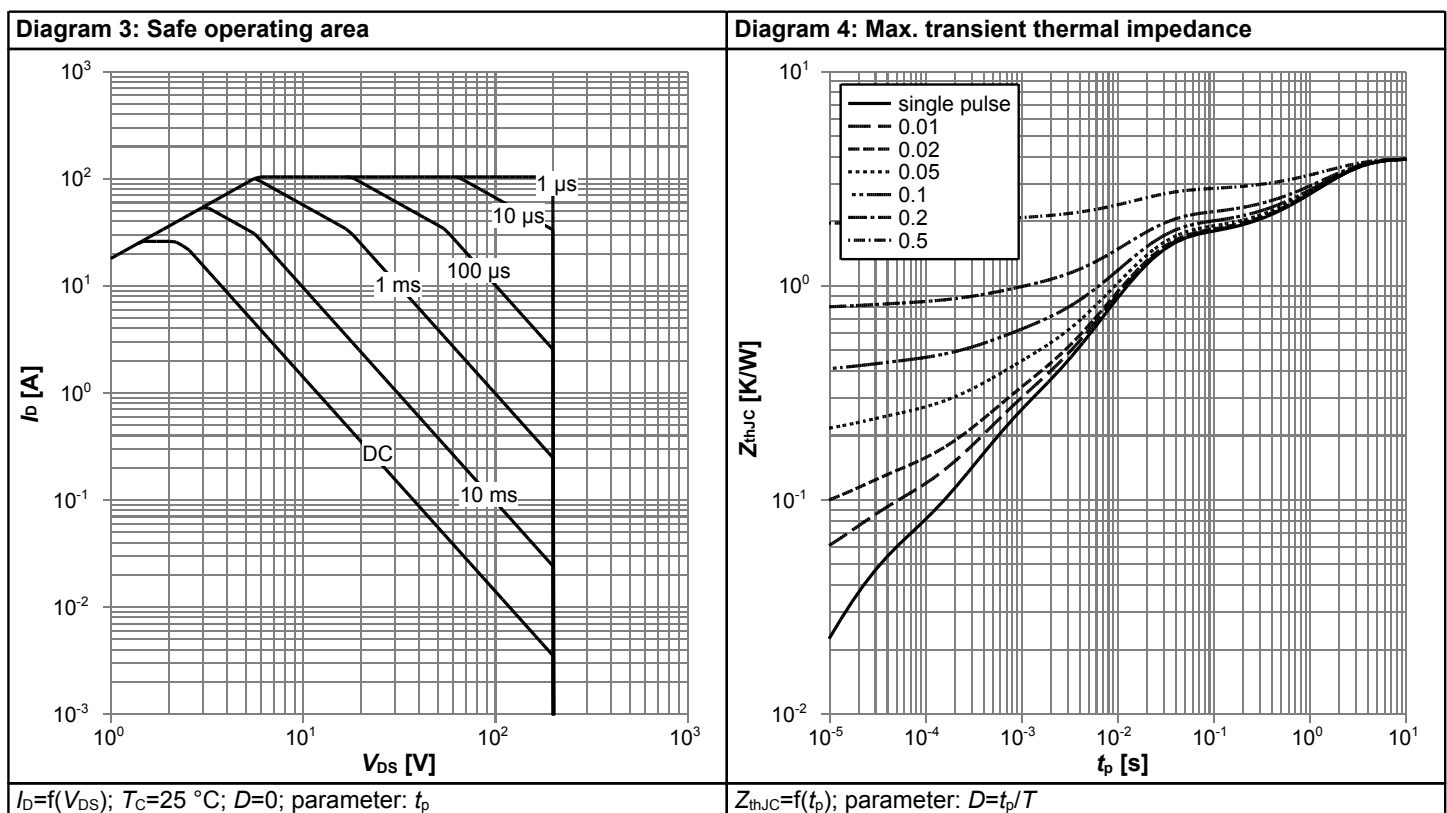
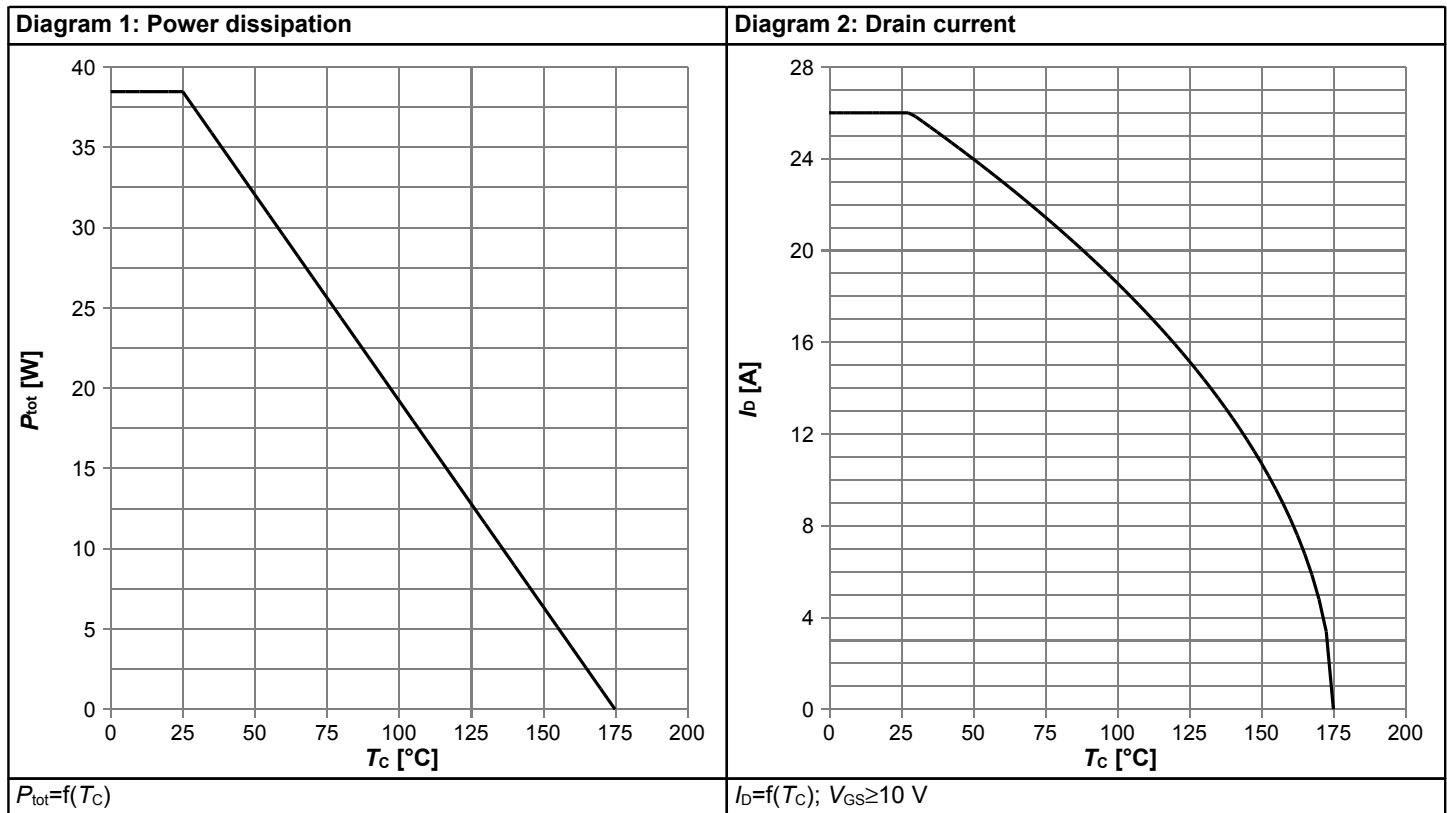
Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	26	A	$T_C=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$	-	-	104	A	$T_C=25\text{ °C}$
Diode forward voltage	V_{SD}	-	0.94	1.2	V	$V_{GS}=0\text{ V}$, $I_F=26\text{ A}$, $T_J=25\text{ °C}$
Reverse recovery charge ¹⁾	Q_{rr}	-	500	-	nC	$V_R=100\text{ V}$, $I_F=13\text{ A}$, $di_F/dt=100\text{ A}/\mu\text{s}$

¹⁾ Defined by design. Not subject to production test.

²⁾ See "Gate charge waveforms" for parameter definition

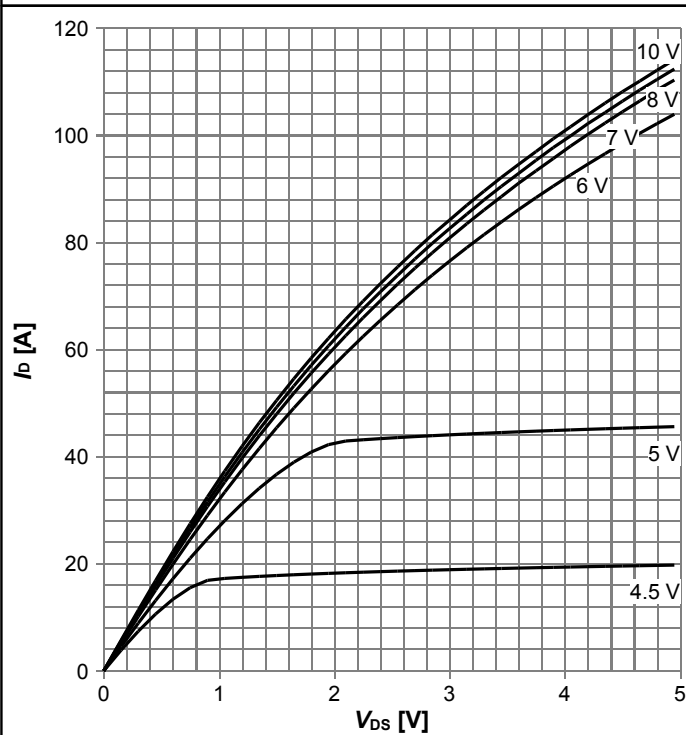
4 Electrical characteristics diagrams



OptiMOS™ 3 Power-Transistor, 200 V

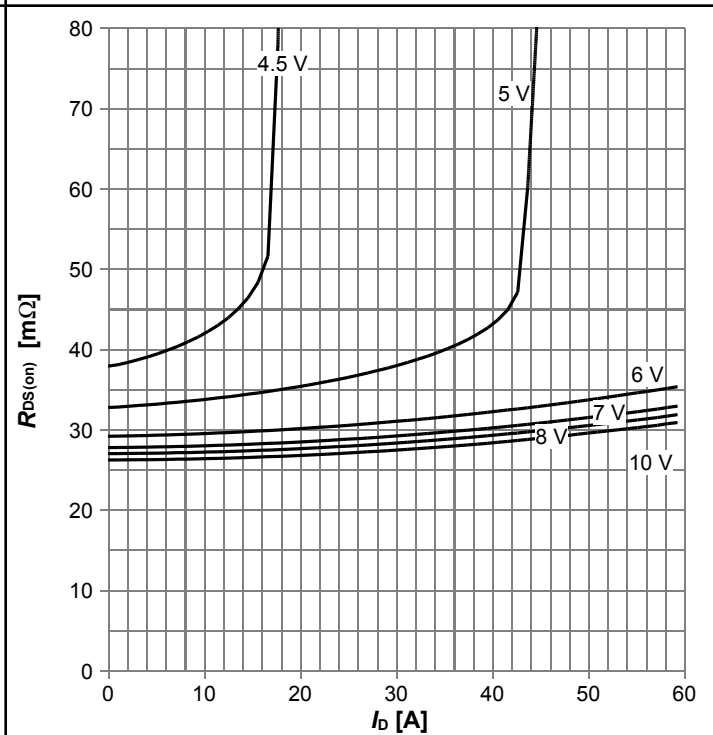
IPA320N20NM3S

Diagram 5: Typ. output characteristics



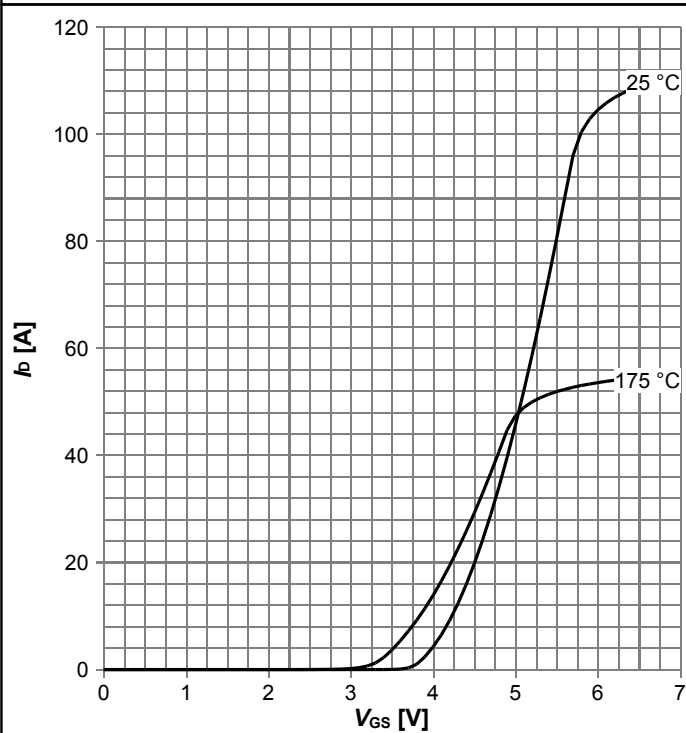
$I_D = f(V_{DS})$, $T_j = 25^\circ\text{C}$; parameter: V_{GS}

Diagram 6: Typ. drain-source on resistance



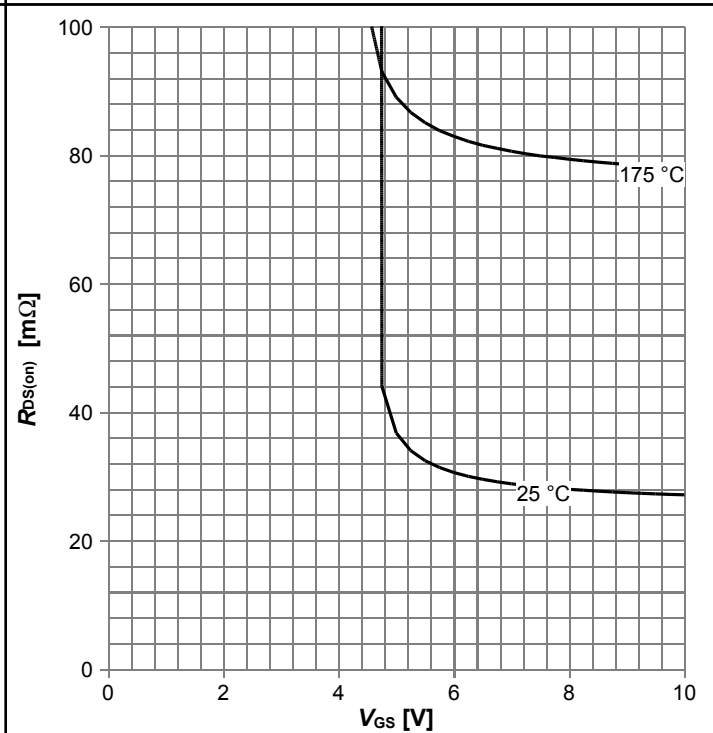
$R_{DS(on)} = f(I_D)$, $T_j = 25^\circ\text{C}$; parameter: V_{GS}

Diagram 7: Typ. transfer characteristics



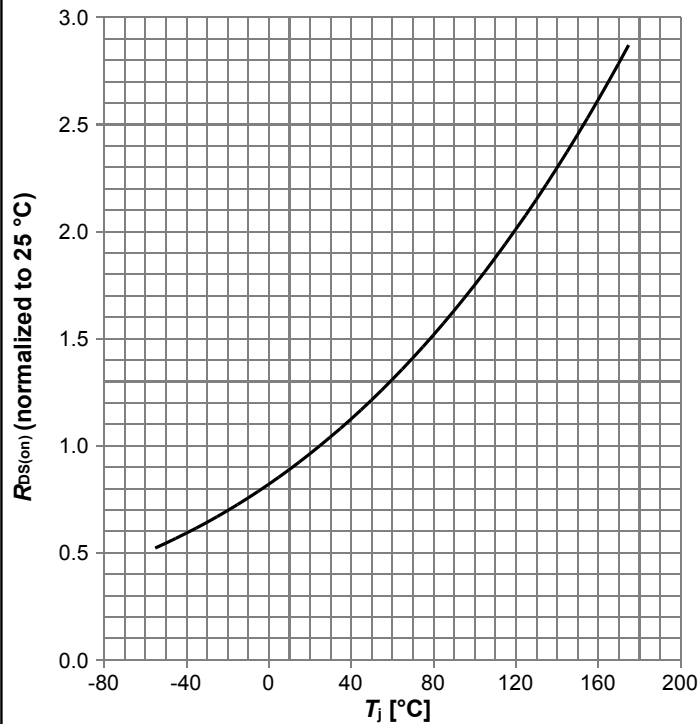
$I_D = f(V_{GS})$, $|V_{DS}| > 2|I_D|R_{DS(on)max}$; parameter: T_j

Diagram 8: Typ. drain-source on resistance



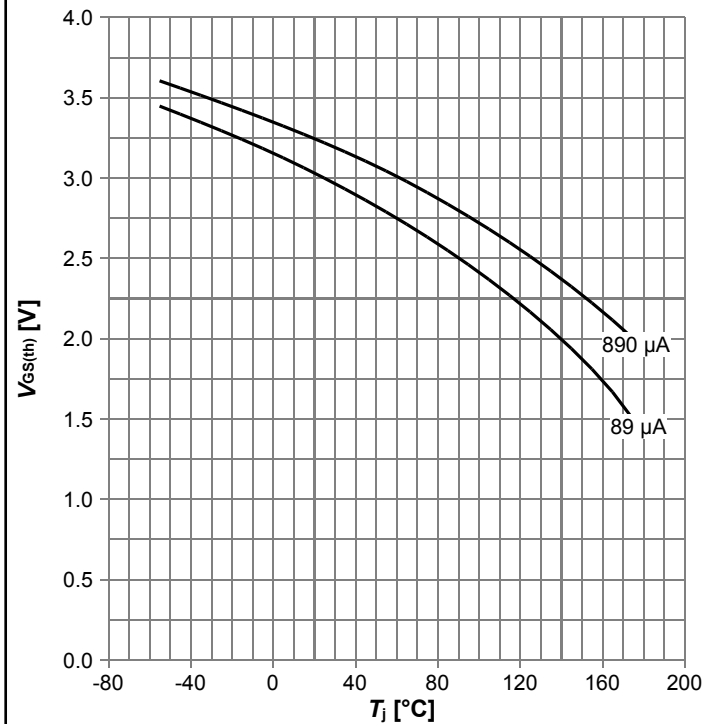
$R_{DS(on)} = f(V_{GS})$, $I_D = 26\text{ A}$; parameter: T_j

Diagram 9: Normalized drain-source on resistance



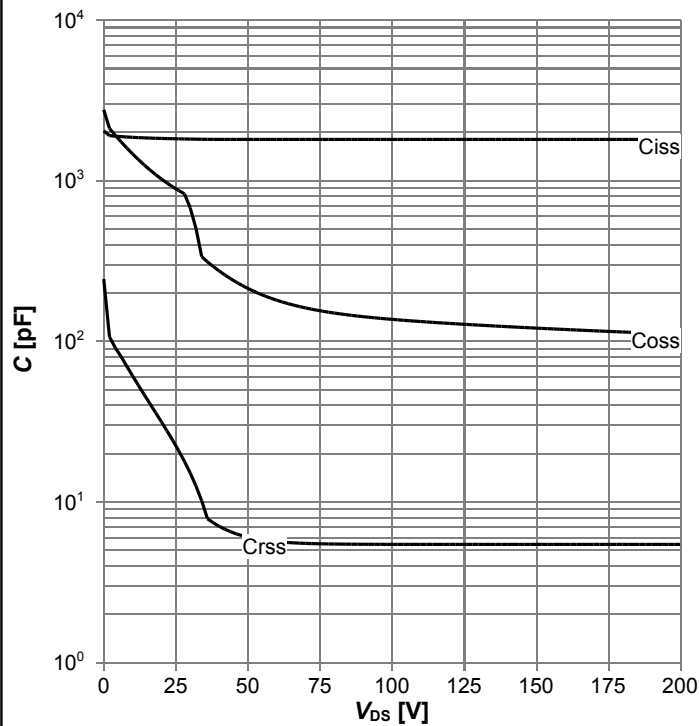
$R_{DS(on)} = f(T_j)$, $I_D = 26 \text{ A}$, $V_{GS} = 10 \text{ V}$

Diagram 10: Typ. gate threshold voltage



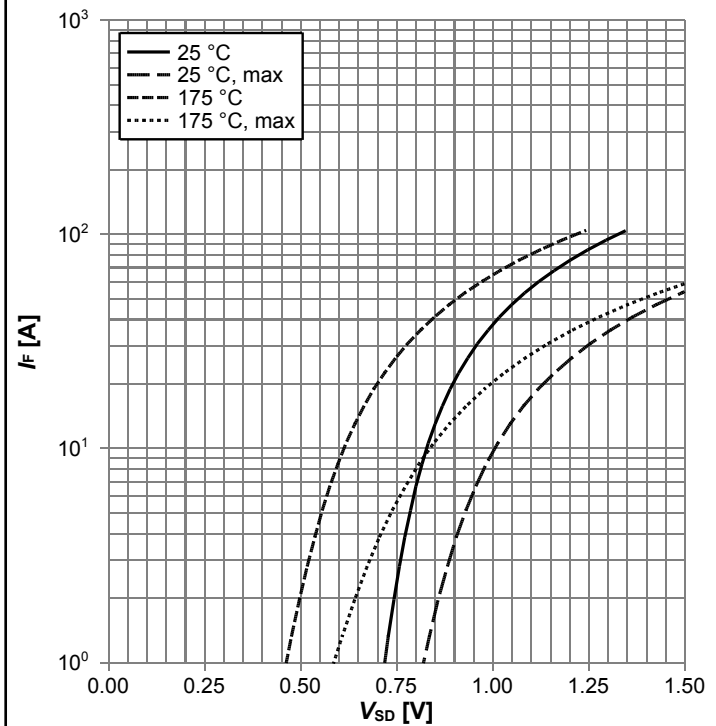
$V_{GS(th)} = f(T_j)$, $V_{GS} = V_{DS}$; parameter: I_D

Diagram 11: Typ. capacitances



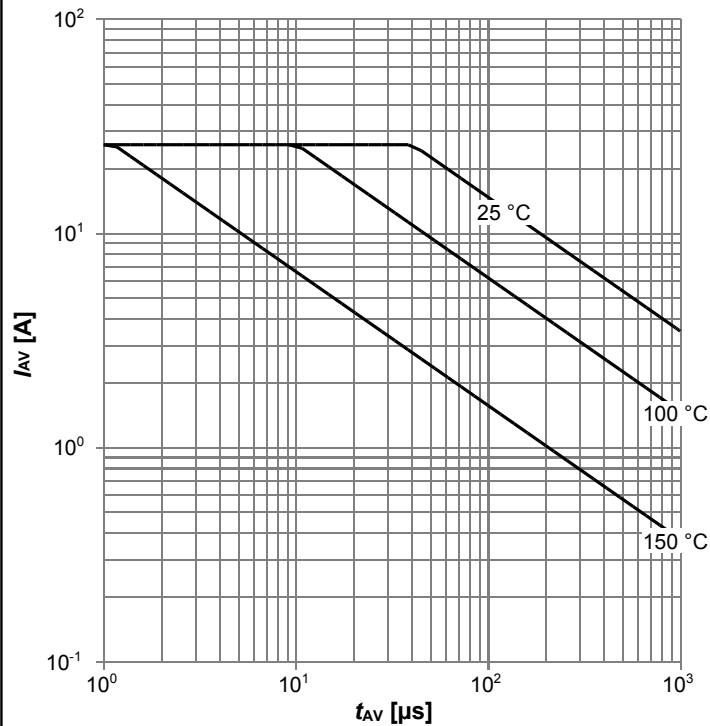
$C = f(V_{DS})$; $V_{GS} = 0 \text{ V}$; $f = 1 \text{ MHz}$

Diagram 12: Forward characteristics of reverse diode



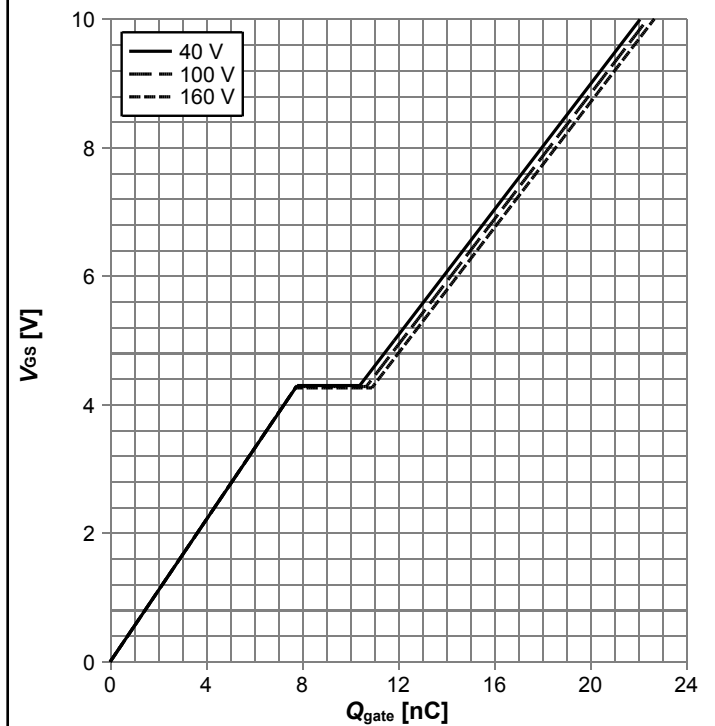
$I_F = f(V_{SD})$; parameter: T_j

Diagram 13: Avalanche characteristics



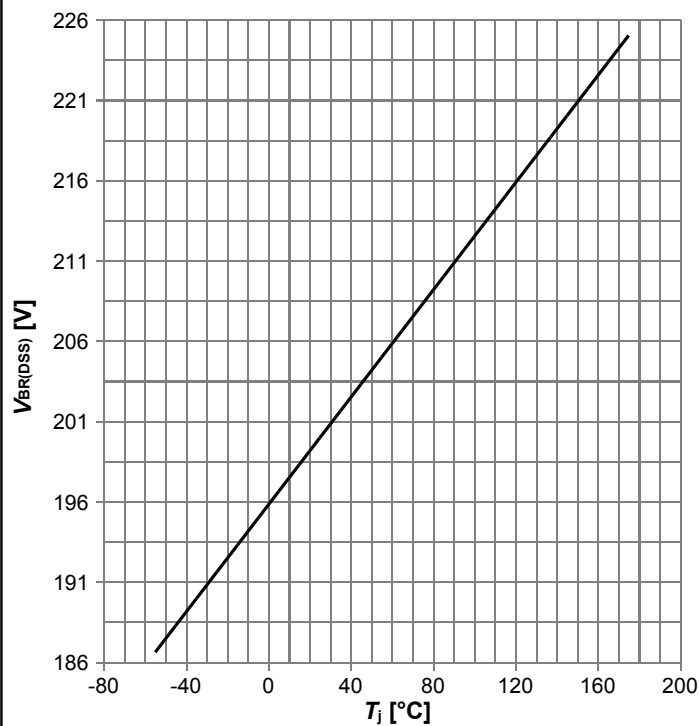
$I_{AS}=f(t_{AV})$; $R_{GS}=25\ \Omega$; parameter: $T_{j,start}$

Diagram 14: Typ. gate charge



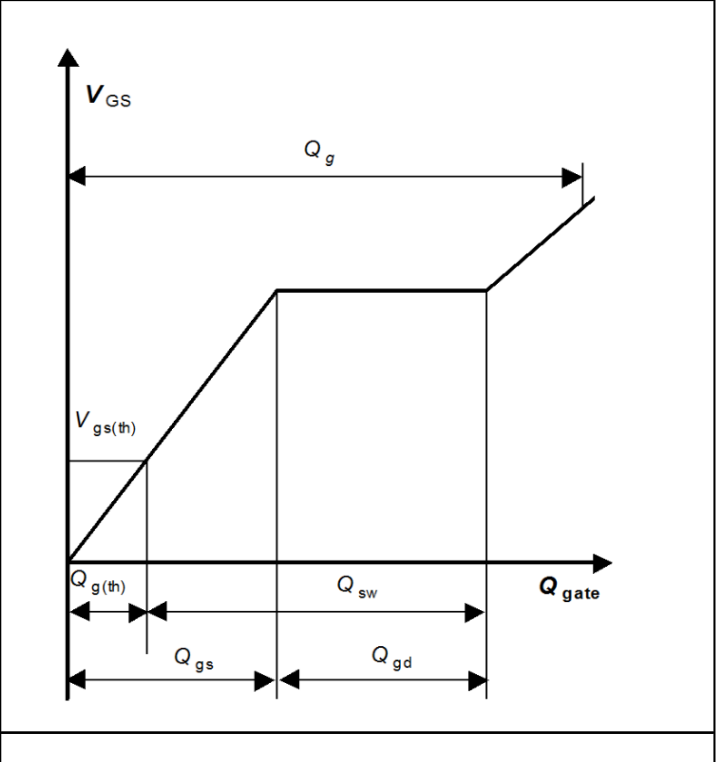
$V_{GS}=f(Q_{gate})$, $I_D=13\text{ A}$ pulsed, $T_j=25\text{ °C}$; parameter: V_{DD}

Diagram 15: Drain-source breakdown voltage

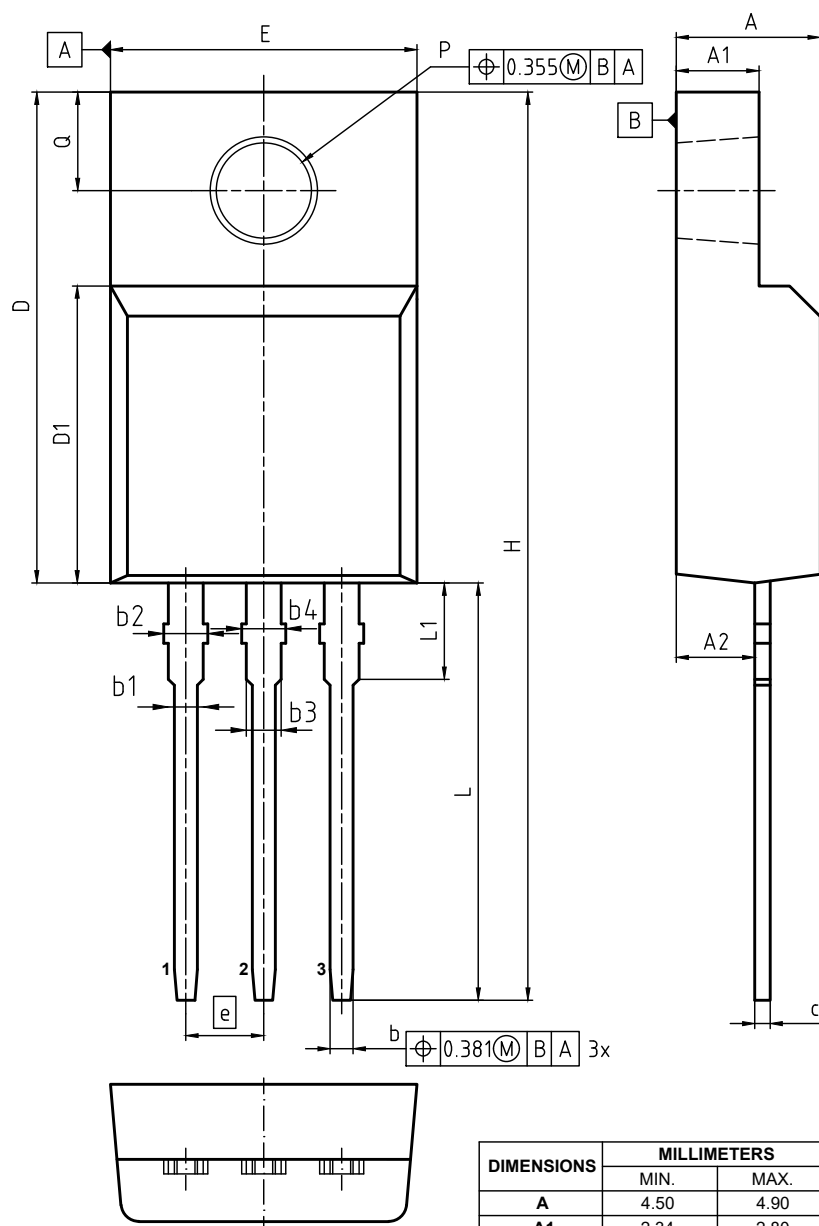


$V_{BR(DSS)}=f(T_j)$; $I_D=1\text{ mA}$

Diagram Gate charge waveforms



5 Package Outlines



NOTES:
STANDARD QUALITY GRADE
DIMENSIONS DO NOT INCLUDE MOLD FLASH, PRO-
TRUSIONS OR GATE BURRS

DIMENSIONS	MILLIMETERS	
	MIN.	MAX.
A	4.50	4.90
A1	2.34	2.80
A2	2.42	2.86
b	0.65	0.90
b1	0.95	1.38
b2	1.20	1.50
b3	0.65	1.38
b4	1.20	1.50
c	0.40	0.63
D	15.67	16.15
D1	8.97	9.83
E	10.00	10.65
e	2.54	
H	28.70	29.75
L	12.78	13.75
L1	2.83	3.45
øP	3.00	3.38
Q	3.15	3.50

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Figure 1 Outline PG-TO 220 FullPAK, dimensions in mm/inches

Revision History

IPA320N20NM3S

Revision: 2019-09-02, Rev. 2.1

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2019-07-18	Release of final version
2.1	2019-09-02	Update package outline

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